

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	413	((dielectric oxide insulat\$3) near (layer film)) and (peripheral near (device\$1 circuit\$1)) and (control\$4 near2 (flash EEPROM))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/04 08:22
L2	279	L1 and thick\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/04 08:13
L3	90	I and (thick\$4 near (dielectric oxide insulat\$3) near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/04 08:15
L4	11	thick\$4 near (dielectric oxide insulat\$3) near (layer film) near peripheral near (device\$1 circuit\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/04 08:30
L5	2231	(thick\$4 near (dielectric oxide insulat\$3) near (layer film)) and (peripheral near (device\$1 circuit\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/04 08:31
L6	3055	(thick\$4 near (dielectric oxide insulat\$3) near (layer film)) and (flash EEPROM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/04 08:32
L7	673	5 and 6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/04 08:32
L8	444	7 and equal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/04 08:32

L9	26	(thick\$4 near (dielectric oxide insulat\$3) near (layer film)) and (peripheral near (device\$1 circuit\$1)) with (thick\$4 near (dielectric oxide insulat\$3) near (layer film)) and (flash EEPROM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/04 08:33
S1	5674	257/239,261,298,315-326.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/30 14:58
S2	4892	438/201,211,216,241,257,258,260-266, 591,593.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/30 14:58
S3	9816	S1 or S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/30 14:58
S4	4635	S3 and (flash EEPROM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/02 12:15
S5	4276	S4 and ((float\$3 control) adj gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/30 16:19
S6	1119	S5 and ((first adj (dielectric oxide insulat\$3)) with (second adj (dielectric oxide insulat\$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/30 15:45
S7	257	S5 and (thick\$4 with (first adj (dielectric oxide insulat\$3)) with (second adj (dielectric oxide insulat\$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/30 15:15
S8	17	S7 and (capacitance near (dielectric oxide insulat\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/30 15:12

S9	9	("4288863" "4425631" "4651406" "4823316" "4851361" "4870615" "4935790" "5225700" "5324677").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/30 15:07
S10	6	("4288863" "4425631" "4823316" "4870615" "4935790" "5225700").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/30 15:11
S11	9	S7 and ((gate near coupl\$3 near ratio) GCR)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/30 15:13
S12	137	S5 and ((different near thick\$4) with (dielectric oxide insulat\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/30 16:18
S13	2	("5393684" "5429960").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/30 15:38
S14	2	("5310693" "5352618").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/30 15:42
S15	3210	S5 and ((dielectric oxide insulat\$3) with first with second)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/02 13:10
S16	195	S5 and ((dielectric oxide insulat\$3) with (first near thick\$4) with (second near thick\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/30 16:28
S17	13	("5065201" "5449941" "5455793" "5629222" "5777359" "5883832" "5929480" "5973357" "6057575" "6147379" "6335716" "6376875" "RE37199").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/30 15:57
S18	8	("4894402" "4924119" "5008721" "5216270" "5460991" "5666307" "5734609" "5838616").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/30 16:10
S19	4	("4209349" "4648937" "5236853" "5371027").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/30 16:17
S20	239000	"257"/\$.ccls. "438"/\$.ccls. "365"/\$.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/30 16:18

S21	437119	"257"/\$.ccls. "438"/\$.ccls. "365"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/30 16:18
S22	1447	S21 and ((different near thick\$4) with (dielectric oxide insulat\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/30 16:18
S23	319	S22 and (flash EEPROM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/30 16:28
S24	256	S23 and ((float\$3 control) adj gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/30 16:28
S25	1750	S21 and ((dielectric oxide insulat\$3) with (first near thick\$4) with (second near thick\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/30 16:28
S26	353	S25 and (flash EEPROM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/30 16:28
S27	285	S26 and ((float\$3 control) adj gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/12/30 16:28
S28	66	cell\$1 with (first near sub near cell\$1) with (second near sub near cell\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/02 12:16
S29	8	("5430679" "5487039" "5502676" "5684746" "5703817" "6188618" "6314032" "6438045").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/01/02 11:29

S30	343243	(flash EEPROM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/02 12:15
S31	25	S30 and (first near sub near cell\$1) with (second near sub near cell\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/02 13:27
S32	524	S30 and (sub near cell\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/02 13:08
S33	53	S32 and ((dielectric oxide insulat\$3) with first with second)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/02 13:10
S34	70	S30 and (first near sub near cell\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/03 08:13
S35	343243	(flash EEPROM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/03 08:13
S36	524	S35 and (sub near cell\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/03 08:13
S37	55	S36 and (first near sub near cell\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/03 08:14
S38	0	((dielectric oxide insulat\$3) near (layer film)) near2 (peripheral near (device\$1 circuit\$1)) near2 control near2 (flash EEPROM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/03 19:22

S39	1	((dielectric oxide insulat\$3) near (layer film)) near2 (peripheral near (device\$1 circuit\$1)) with control\$4 near2 (flash EEPROM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/03 19:25
S40	412	((dielectric oxide insulat\$3) near (layer film)) and (peripheral near (device\$1 circuit\$1)) and (control\$4 near2 (flash EEPROM))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/04 08:13
S41	13	((dielectric oxide insulat\$3) near (layer film)) same (peripheral near (device\$1 circuit\$1)) same (control\$4 near2 (flash EEPROM))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/03 19:30
S42	3	(thick\$4 near (dielectric oxide insulat\$3) near (layer film)) same (peripheral near (device\$1 circuit\$1)) same (control\$4 near2 (flash EEPROM))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/03 19:32
S43	90	(thick\$4 near (dielectric oxide insulat\$3) near (layer film)) and (peripheral near (device\$1 circuit\$1)) and (control\$4 near2 (flash EEPROM))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/04 08:15